

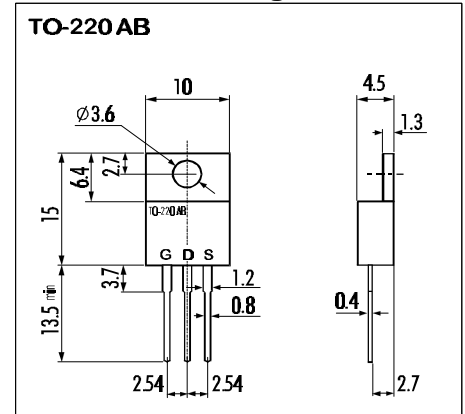
> **Features**

- High Current
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- High Forward Transconductance

> **Applications**

- Motor Control
- General Purpose Power Amplifier
- DC-DC converters

> **Outline Drawing**

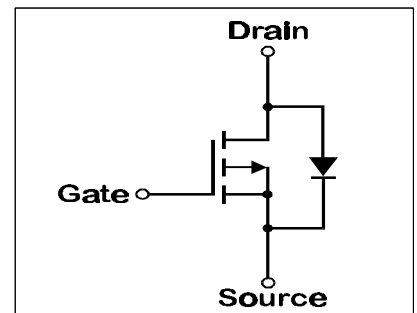


> **Maximum Ratings and Characteristics**

- Absolute Maximum Ratings (T_C=25°C), unless otherwise specified

Item	Symbol	Rating	Unit
Drain-Source-Voltage	V _{DS}	-60	V
Continous Drain Current	I _D	25	A
Pulsed Drain Current	I _{D(puls)}	100	A
Gate-Source-Voltage	V _{GS}	±20	V
Maximum Avalanche Energy	E _{AV}	325,9	mJ
Max. Power Dissipation	P _D	50	W
Operating and Storage Temperature Range	T _{ch}	150	°C
	T _{stg}	-55 ~ +150	°C

> **Equivalent Circuit**



- Electrical Characteristics (T_C=25°C), unless otherwise specified

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown-Voltage	V _{(BR)DSS}	I _D =-1mA V _{GS} =0V	-60			V
Gate Threshold Voltage	V _{GS(th)}	I _D =-1mA V _{DS} =V _{GS}	-1,0	-1,5	-2,5	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V T _{ch} =25°C		-10	-500	μA
		V _{GS} =0V T _{ch} =125°C		-0,2	-1,0	mA
Gate Source Leakage Current	I _{GSS}	V _{GS} =±20V V _{DS} =0V		10	100	nA
Drain Source On-State Resistance	R _{DS(on)}	I _D =-12,5A V _{GS} =-4V		0,08	0,11	Ω
		I _D =-12,5A V _{GS} =-10V		0,045	0,06	Ω
Forward Transconductance	g _{fs}	I _D =-12,5A V _{DS} =-25V	7,5	15		S
Input Capacitance	C _{iss}	V _{DS} =-25V		2000	3000	pF
Output Capacitance	C _{oss}	V _{GS} =0V		700	1050	pF
Reverse Transfer Capacitance	C _{rss}	f=1MHz		450	680	pF
Turn-On-Time t _{on} (t _{on} =t _{d(on)} +t _r)	t _{d(on)}	V _{CC} =-30V		15	25	ns
	t _r	I _D =-25A		80	120	ns
Turn-Off-Time t _{off} (t _{off} =t _{d(off)} +t _f)	t _{d(off)}	V _{GS} =-10V		190	290	ns
	t _f	R _{GS} =10 Ω		90	140	ns
Avalanche Capability	I _{AV}	L=100μH T _{ch} =25°C	-25			A
Diode Forward On-Voltage	V _{SD}	I _F =2xI _{DR} V _{GS} =0V T _{ch} =25°C		-2,0	-3,0	V
Reverse Recovery Time	t _{rr}	I _F =I _{DR} V _{GS} =0V		160		ns
Reverse Recovery Charge	Q _{rr}	-dI _F /dt=100A/μs T _{ch} =25°C		0,9		μC

- Thermal Characteristics

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Thermal Resistance	R _{th(ch-a)}	channel to air			75	°C/W
	R _{th(ch-c)}	channel to case			2,50	°C/W

P-channel MOS-FET			
-60V	0,06Ω	25A	50W

2SJ475-01

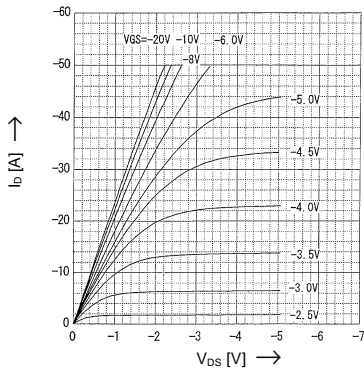
FAP-III Series



> Characteristics

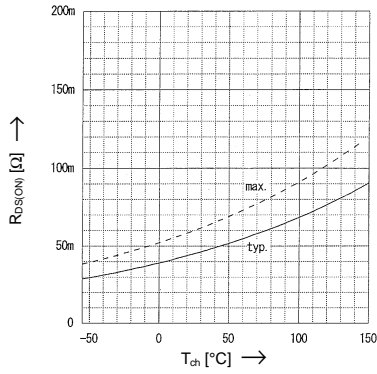
Typical Output Characteristics

$I_D = f(V_{DS})$; 80μs pulse test; $T_C = 25^\circ\text{C}$



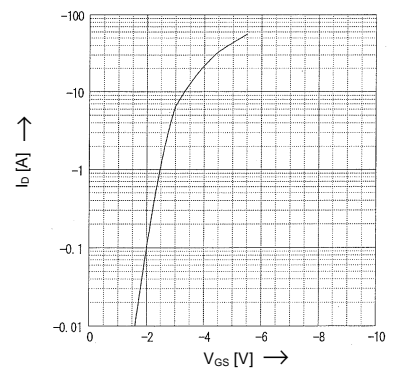
Drain-Source On-State Resistance vs. T_{ch}

$R_{DS(on)} = f(T_{ch})$; $I_D = 12.5\text{A}$; $V_{GS} = 10\text{V}$



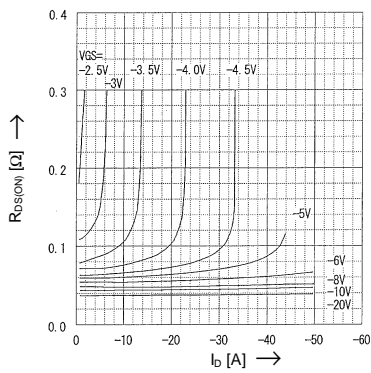
Typical Transfer Characteristics

$I_D = f(V_{GS})$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



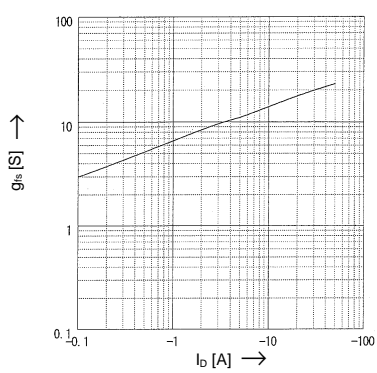
Typical Drain-Source On-State-Resistance vs. I_D

$R_{DS(on)} = f(I_D)$; 80μs pulse test; $T_C = 25^\circ\text{C}$



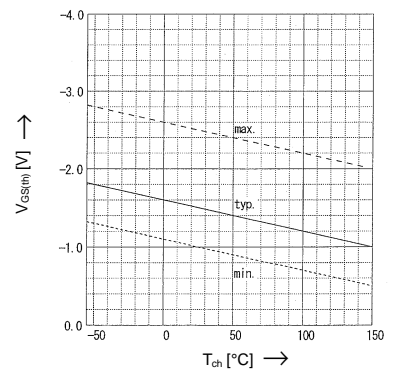
Typical Forward Transconductance vs. I_D

$g_s = f(I_D)$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



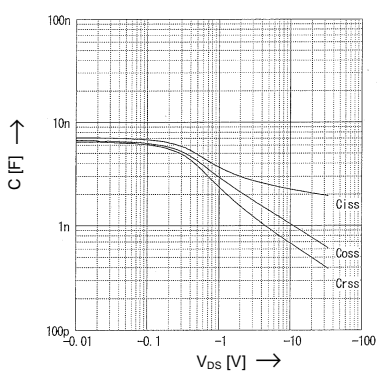
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)} = f(T_{ch})$; $I_D = 1\text{mA}$; $V_{DS} = V_{GS}$



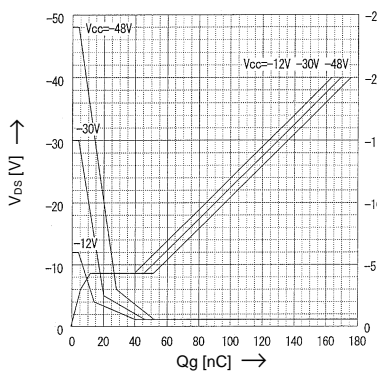
Typical Capacitances vs. V_{DS}

$C = f(V_{DS})$; $V_{GS} = 0\text{V}$; $f = 1\text{MHz}$



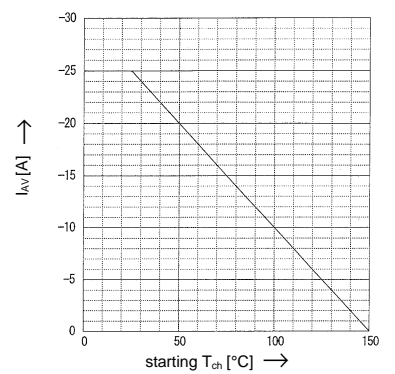
Typical Gate Charge Characteristic

$V_{GS} = f(Q_g)$; $I_D = 25\text{A}$; $T_C = 25^\circ\text{C}$



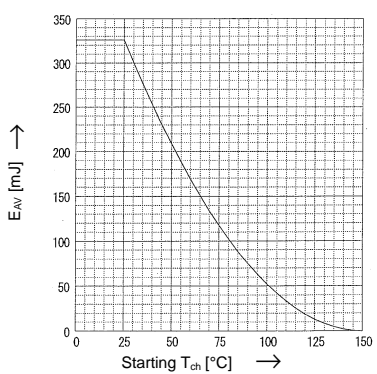
Maximum Avalanche Current vs. starting T_{ch}

$I_{AV} = f(\text{starting } T_{ch})$



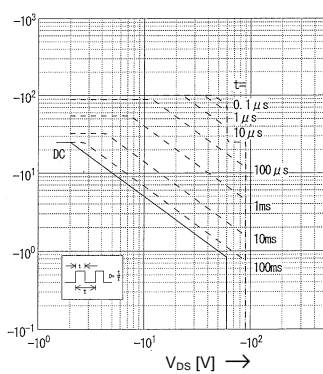
Maximum Avalanche Energy vs. starting T_{ch}

$E_{AV} = f(\text{starting } T_{ch})$; $V_{CC} = 24\text{V}$; $I_{AV} > 25\text{A}$



Safe Operation Area

$I_D = f(V_{DS})$; $D = 0.01$; $T_C = 25^\circ\text{C}$



$Z_{th(ch-e)}$ [K/W]

Transient Thermal impedance

$Z_{th(ch)} = f(t)$ parameter: $D = t/T$

